Resolution Plot

DESIGN MSX25-1000

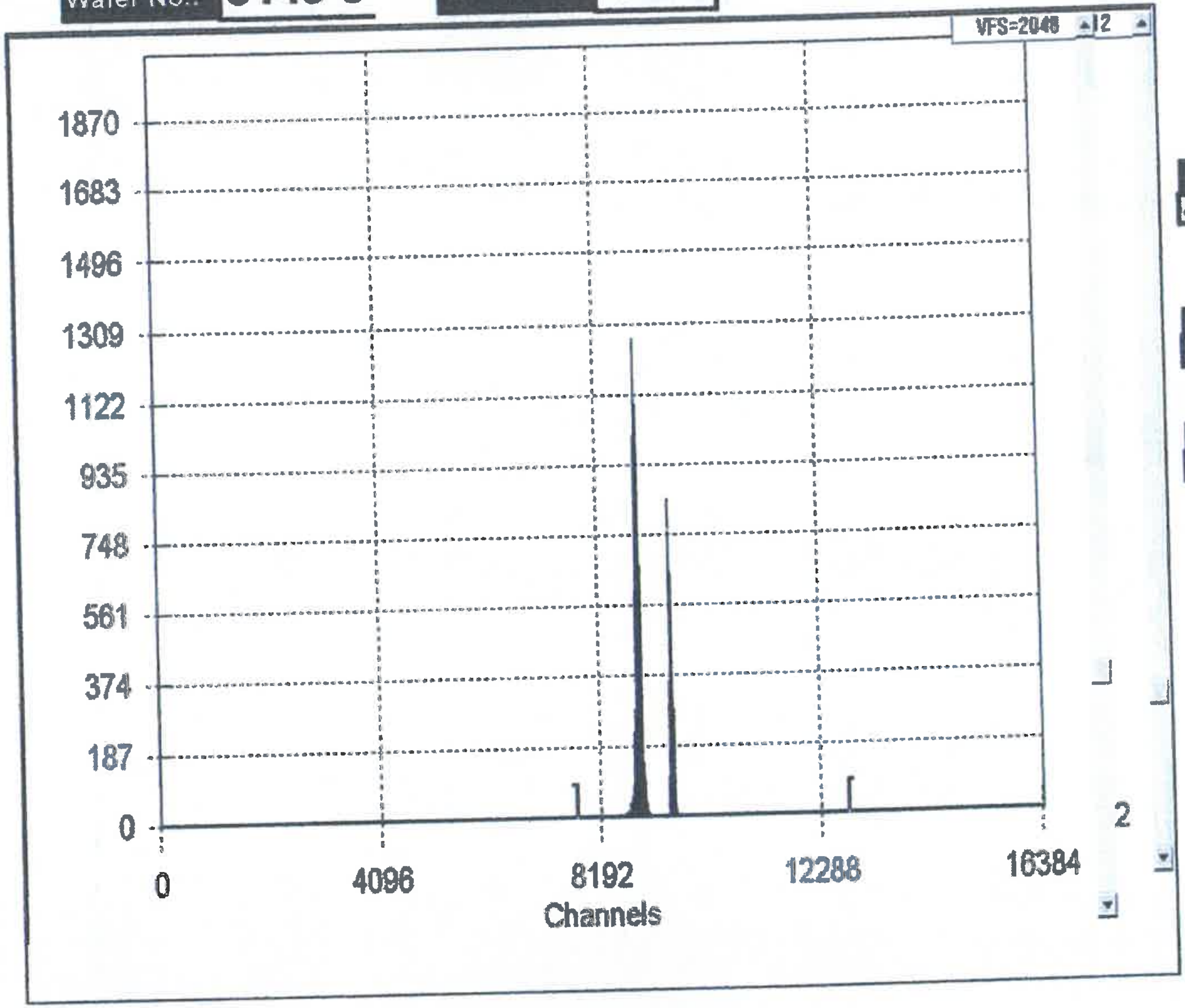
Wafer No.: **3145-8** Thickness: **1029** um

UNCTION

ET LINE: 40.5 KeV
YSTEM: 25.4 KeV
AL: 31.5 KeV

OHMIC

DET LINE: 45.8 KeV
SYSTEM: 25.5 KeV
CALC: 38.1 KeV



Source: Am 241

Rise Time: 1

Flat Top: 0

T=22.2DC

BIAS VOLTS= 120 V Leakage 184 nA

Micron Semiconductor
01/12/2014

CUSTOMER: STOCK
PURCHASE ORDER NUMBER:
DEVICE TYPE: MSX25-1000
DATE: 27/11/2014

MEASUREMENT DATA IN AIR:

TEMPERATURE: 22^{o}c
HUMIDITY: 42%

DEVICE NUMBER	THICKNESS	OPERATING VOLTAGE	IR @ DEP.	IR @ DEP.+30V	VB @ 10uA	VF @ 10mA
3145-8	1029uM	175V	184nA	211nA	>200V	0.52V